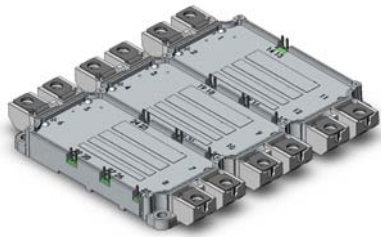


SEMiX503GD126HDc



SEMiX[®] 33c

Trench IGBT Modules

SEMiX503GD126HDc

Features

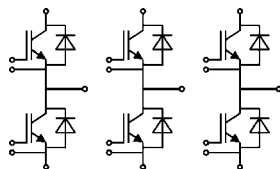
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperatur limited to $T_C=125^{\circ}C$ max.
- Not for new design

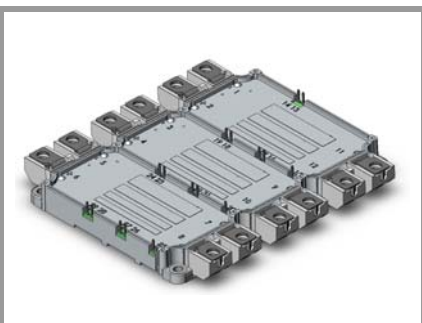


GD

Absolute Maximum Ratings				
Symbol	Conditions	Values	Unit	
IGBT				
V_{CES}		1200	V	
I_C	$T_j = 150^{\circ}C$	$T_c = 25^{\circ}C$	466	A
		$T_c = 80^{\circ}C$	327	A
I_{Cnom}		300	A	
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	600	A	
V_{GES}		-20 ... 20	V	
t_{psc}	$V_{CC} = 600 V$ $V_{GE} \leq 20 V$ $V_{CES} \leq 1200 V$	$T_j = 125^{\circ}C$	10	μs
T_j		-40 ... 150	$^{\circ}C$	
Inverse diode				
I_F	$T_j = 150^{\circ}C$	$T_c = 25^{\circ}C$	412	A
		$T_c = 80^{\circ}C$	284	A
I_{Fnom}		300	A	
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	600	A	
I_{FSM}	$t_p = 10 ms, \sin 180^{\circ}, T_j = 25^{\circ}C$	2000	A	
T_j		-40 ... 150	$^{\circ}C$	
Module				
$I_{t(RMS)}$		600	A	
T_{stg}		-40 ... 125	$^{\circ}C$	
V_{isol}	AC sinus 50Hz, t = 1 min	4000	V	

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 300 A$ $V_{GE} = 15 V$ chipelevel	$T_j = 25^{\circ}C$	1.7	2.1	V
		$T_j = 125^{\circ}C$	2	2.45	V
V_{CE0}		$T_j = 25^{\circ}C$	1	1.2	V
		$T_j = 125^{\circ}C$	0.9	1.1	V
r_{CE}	$V_{GE} = 15 V$	$T_j = 25^{\circ}C$	2.3	3.0	m Ω
		$T_j = 125^{\circ}C$	3.7	4.5	m Ω
$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C = 12 mA$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0 V$ $V_{CE} = 1200 V$	$T_j = 25^{\circ}C$	0.1	0.3	mA
		$T_j = 125^{\circ}C$			mA
C_{ies}	$V_{CE} = 25 V$		21.6		nF
C_{oes}	$V_{GE} = 0 V$		1.13		nF
C_{res}			0.98		nF
Q_G	$V_{GE} = - 8 V...+ 15 V$		2400		nC
R_{Gint}	$T_j = 25^{\circ}C$		2.50		Ω
$t_{d(on)}$	$V_{CC} = 600 V$	$T_j = 125^{\circ}C$	275		ns
t_r	$I_C = 300 A$	$T_j = 125^{\circ}C$	55		ns
		$T_j = 125^{\circ}C$	28		mJ
E_{on}	$R_{G on} = 2.2 \Omega$	$T_j = 125^{\circ}C$	625		ns
$t_{d(off)}$	$R_{G off} = 2.2 \Omega$	$T_j = 125^{\circ}C$	125		ns
t_f		$T_j = 125^{\circ}C$	44		mJ
E_{off}		$T_j = 125^{\circ}C$			
$R_{th(j-c)}$	per IGBT			0.08	K/W

SEMiX503GD126HDc



SEMiX® 33c

Trench IGBT Modules

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Features

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- High short circuit capability
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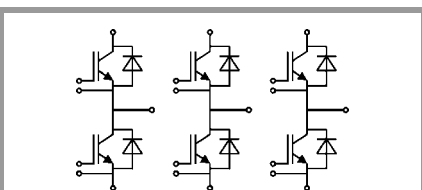
Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperatur limited to $T_C=125^\circ\text{C}$ max.
- Not for new design

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 300\text{ A}$ $V_{GE} = 0\text{ V}$ chip	$T_j = 25^\circ\text{C}$		1.6	1.80	V
		$T_j = 125^\circ\text{C}$		1.6	1.8	V
V_{F0}		$T_j = 25^\circ\text{C}$	0.9	1	1.1	V
		$T_j = 125^\circ\text{C}$	0.7	0.8	0.9	V
r_F		$T_j = 25^\circ\text{C}$	1.7	2.0	2.3	m Ω
		$T_j = 125^\circ\text{C}$	2.3	2.7	3.0	m Ω
I_{RRM}	$I_F = 300\text{ A}$	$T_j = 125^\circ\text{C}$		400		A
Q_{rr}	$di/dt_{off} = 6900\text{ A}/\mu\text{s}$	$T_j = 125^\circ\text{C}$		77		μC
E_{rr}	$V_{GE} = -15\text{ V}$ $V_{CC} = 600\text{ V}$	$T_j = 125^\circ\text{C}$		32.5		mJ
$R_{th(j-c)}$	per diode				0.14	K/W
Module						
L_{CE}				20		nH
$R_{CC'+EE'}$	res., terminal-chip	$T_C = 25^\circ\text{C}$		0.7		m Ω
		$T_C = 125^\circ\text{C}$		1		m Ω
$R_{th(c-s)}$	per module			0.014		K/W
M_s	to heat sink (M5)		3		5	Nm
M_t		to terminals (M6)	2.5		5	Nm
						Nm
w					900	g
Temperatur Sensor						
R_{100}	$T_C=100^\circ\text{C}$ ($R_{25}=5\text{ k}\Omega$)			$493 \pm 5\%$		Ω
$B_{100/125}$	$R_{(T)}=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$; $T[\text{K}]$;			3550 $\pm 2\%$		K



GD

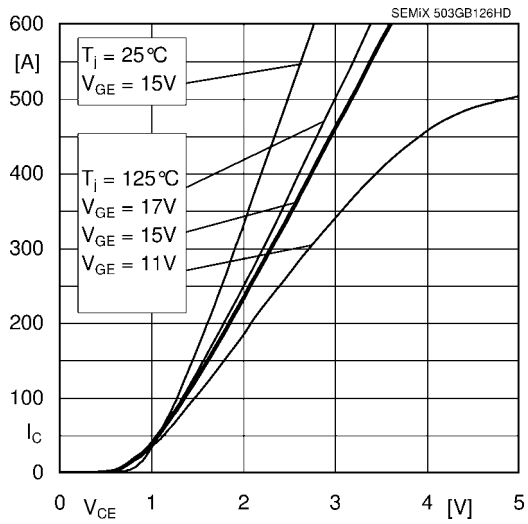


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

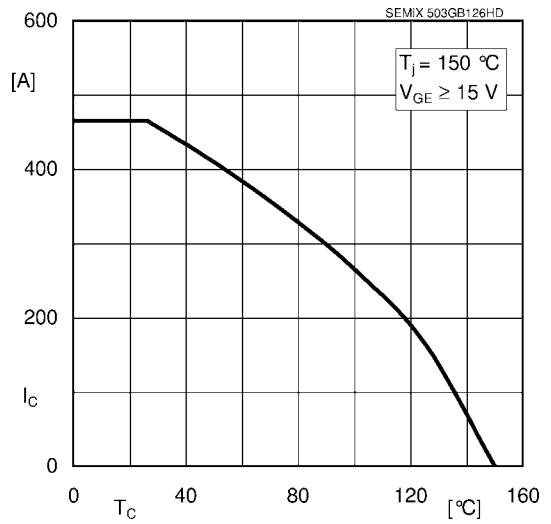


Fig. 2: Rated current vs. temperature $I_c = f(T_c)$

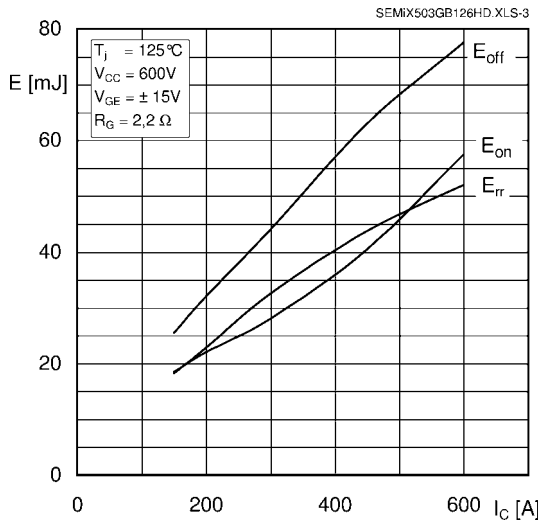


Fig. 3: Typ. turn-on /-off energy = $f(I_c)$

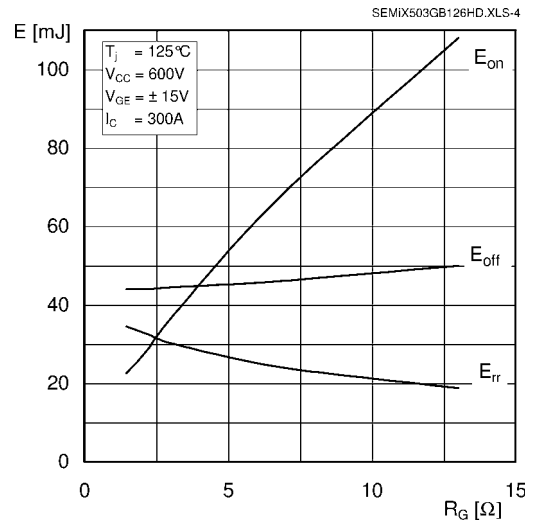


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

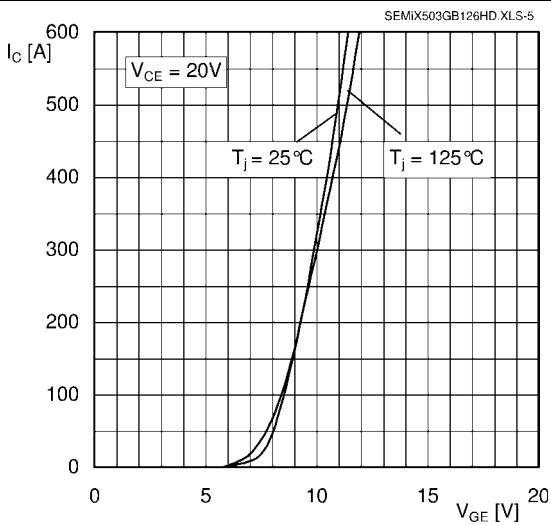


Fig. 5: Typ. transfer characteristic

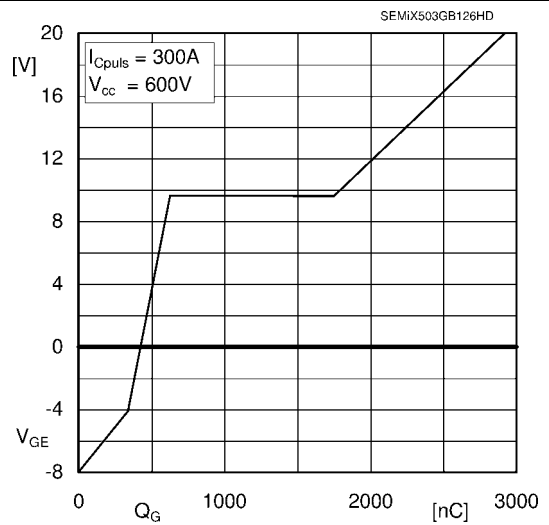


Fig. 6: Typ. gate charge characteristic

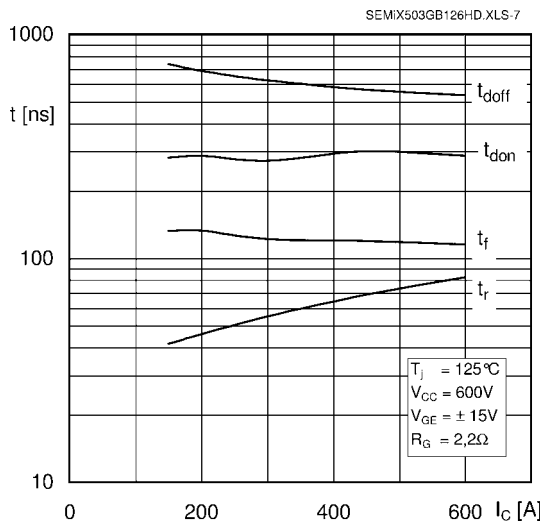


Fig. 7: Typ. switching times vs. I_C

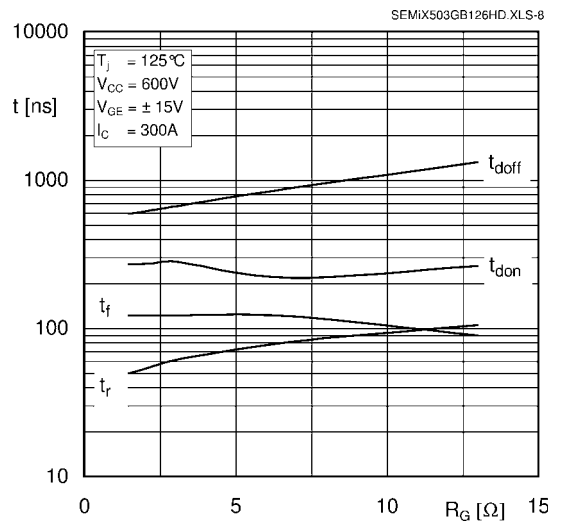


Fig. 8: Typ. switching times vs. gate resistor R_G

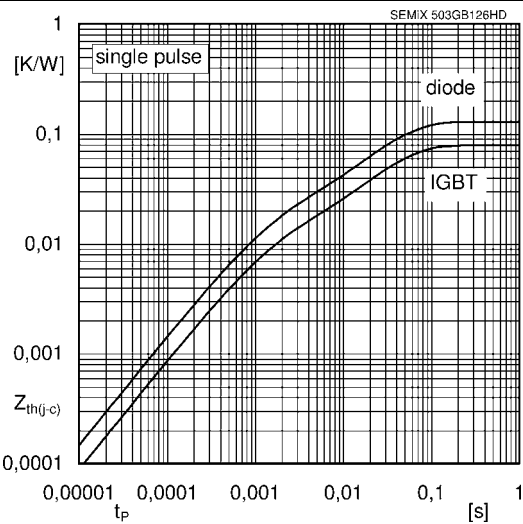


Fig. 9: Typ. transient thermal impedance

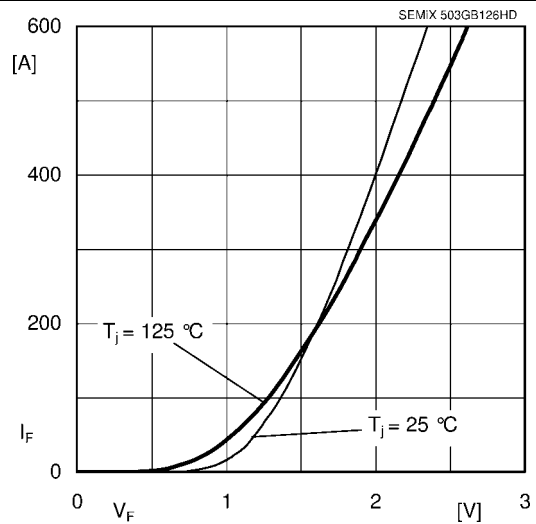


Fig. 10: Typ. CAL diode forward charact., incl. R_{CC+EE}

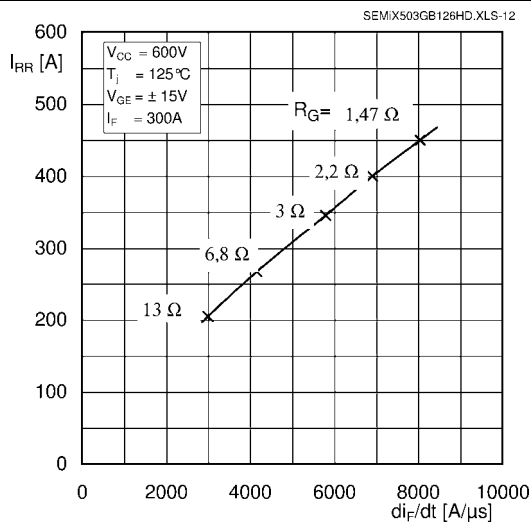


Fig. 11: Typ. CAL diode peak reverse recovery current

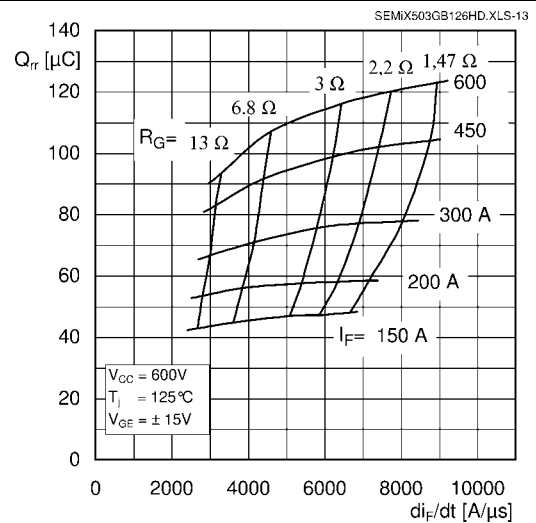


Fig. 12: Typ. CAL diode recovery charge

